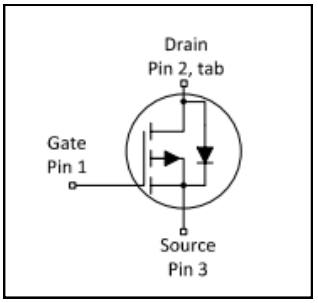
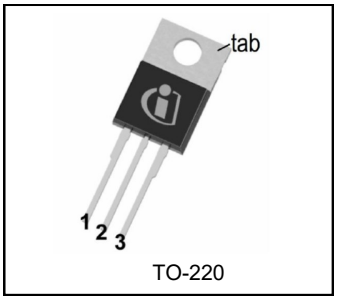
IRF5305PbF

$V_{(BR)DSS}$	-55V
$R_{DS(on)}$ max.	0.06Ω
I_D	-31A





Features

- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- P-Channel
- Fully Avalanche Rated
- Lead-Free

Description

Fifth Generation HEXFET Power MOSFETs utilizes advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of other applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of TO-220 contributes to the wide acceptance throughout the industry.

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF5305NPbF	TO-220	Tube	50	IRF5305PbF

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ -10V	-31	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ -10V	-22	
I_{DM}	Pulsed Drain Current ①	-110	
P_D @T_C = 25°C	Maximum Power Dissipation	110	W
	Linear Derating Factor	0.71	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	280	mJ
I_{AR}	Avalanche Current ①	-16	A
E_{AR}	Repetitive Avalanche Energy ①	11	mJ
dv/dt	Peak Diode Recovery dv/dt③	-5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.4	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	62	

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-55	—	—	V	V_{GS} = 0V, I_D = -250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.034	—	V/°C	Reference to 25°C, I_D = -1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.06	Ω	V_{GS} = -10V, I_D = -16A ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	V_{DS} = V_{GS}, I_D = -250µA
gfs	Forward Trans conductance	8.0	—	—	S	V_{DS} = -25V, I_D = -16A④
I_{DSS}	Drain-to-Source Leakage Current	—	—	-25	µA	V_{DS} = -55V, V_{GS} = 0V
		—	—	-250		V_{DS} = -44V,V_{GS} = 0V,T_J =150°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V_{GS} = -20V
	Gate-to-Source Reverse Leakage	—	—	100		V_{GS} = 20V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Q_g	Total Gate Charge	—	—	63	nC	I_D = -16A
Q_{gs}	Gate-to-Source Charge	—	—	13		V_{DS} = -44V
Q_{gd}	Gate-to-Drain Charge	—	—	29		V_{GS} = -10V, See Fig.6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	V_{DD} = -28V
t_r	Rise Time	—	66	—		I_D = -16A
$t_{d(off)}$	Turn-Off Delay Time	—	39	—		R_G= 6.8Ω
t_f	Fall Time	—	63	—		R_D= 1.6Ω , See Fig.10④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	1200	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	520	—		V_{DS} = -25V
C_{rss}	Reverse Transfer Capacitance	—	250	—		f = 1.0MHz, See Fig.5

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-31	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-110		
V_{SD}	Diode Forward Voltage	—	—	-1.3	V	T_J = 25°C,I_S = -16A,V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	71	110	ns	T_J = 25°C ,I_F = -16A
Q_{rr}	Reverse Recovery Charge	—	170	250	nC	di/dt = 100A/µs ④

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).

② V_{DD} = -25V, Starting T_J = 25°C, L = 2.1mH, R_G = 25Ω, I_{AS} = -16A.(See fig. 12).

③ I_{SD} ≤ -16A, di/dt ≤ -280A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 175°C.

④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

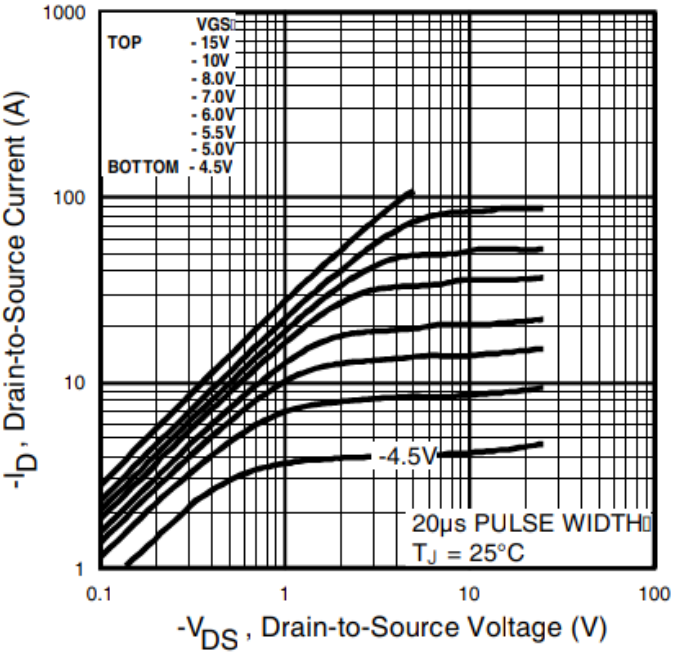


Fig. 1 Typical Output Characteristics

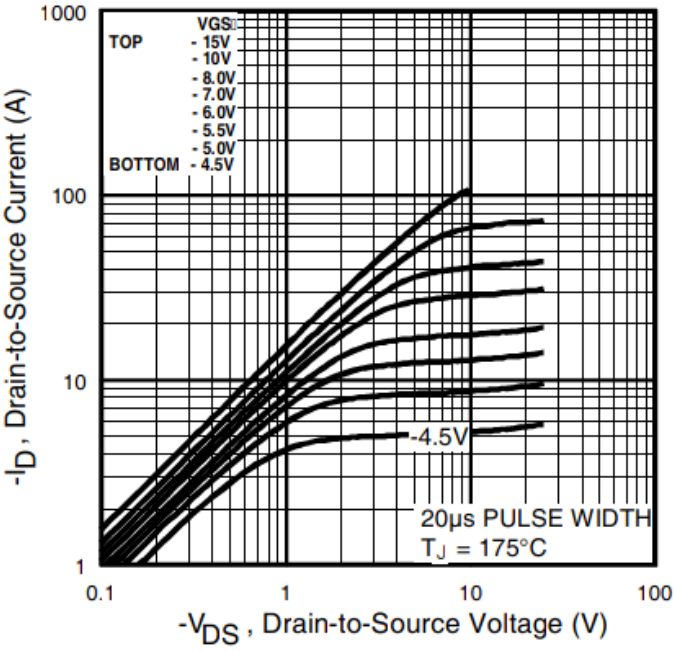


Fig. 2 Typical Output Characteristics

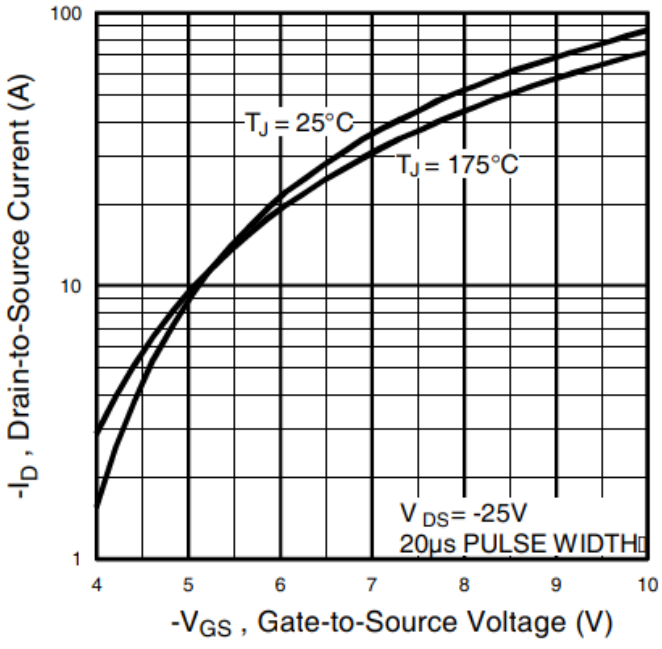


Fig. 3 Typical Transfer Characteristics

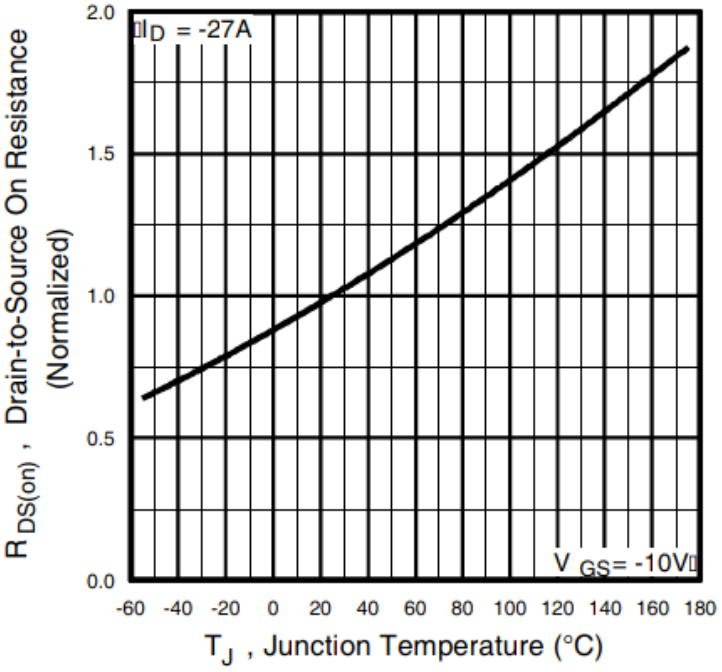


Fig. 4 Normalized On-Resistance vs. Temperature

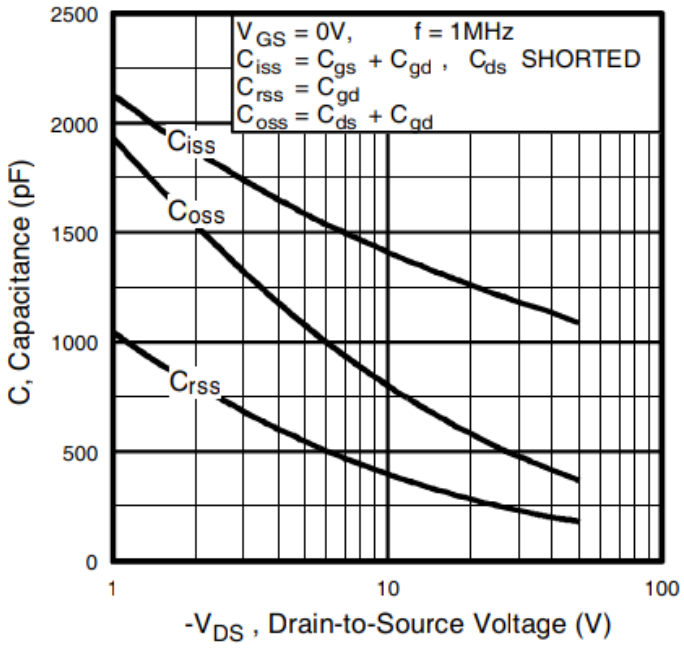


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

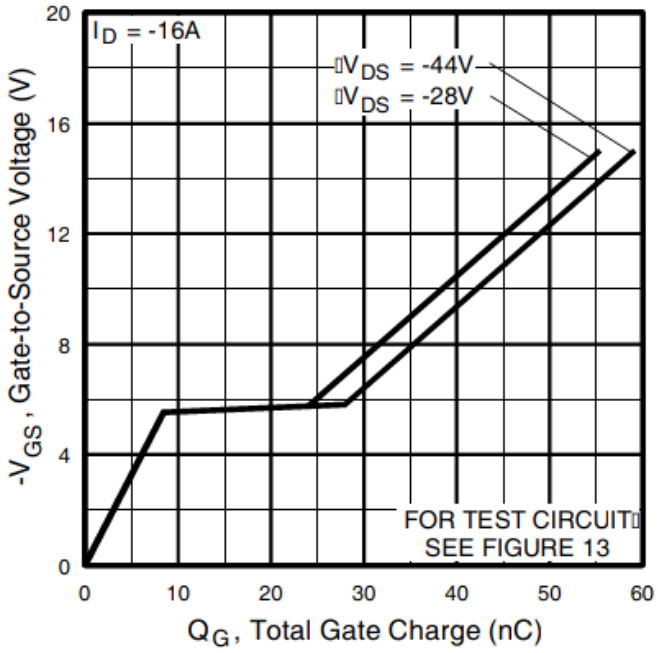


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

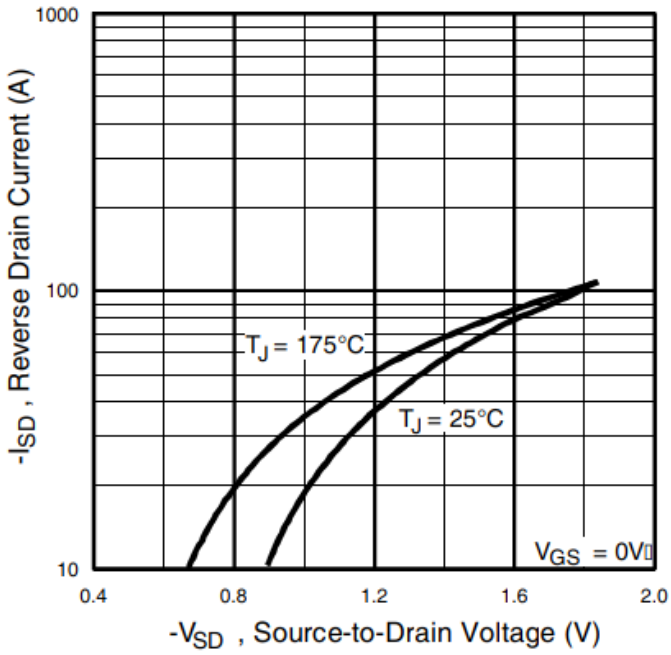


Fig. 7 Typical Source-to-Drain Diode Forward Voltage

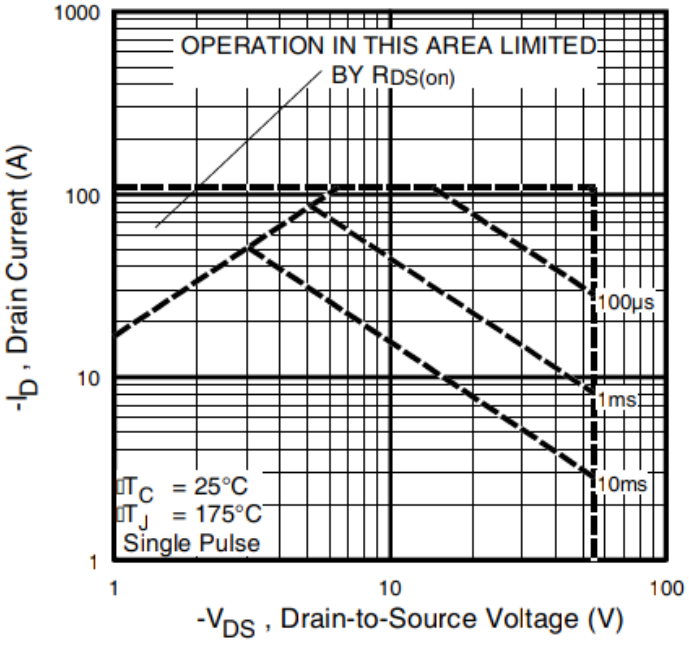


Fig 8. Maximum Safe Operating Area

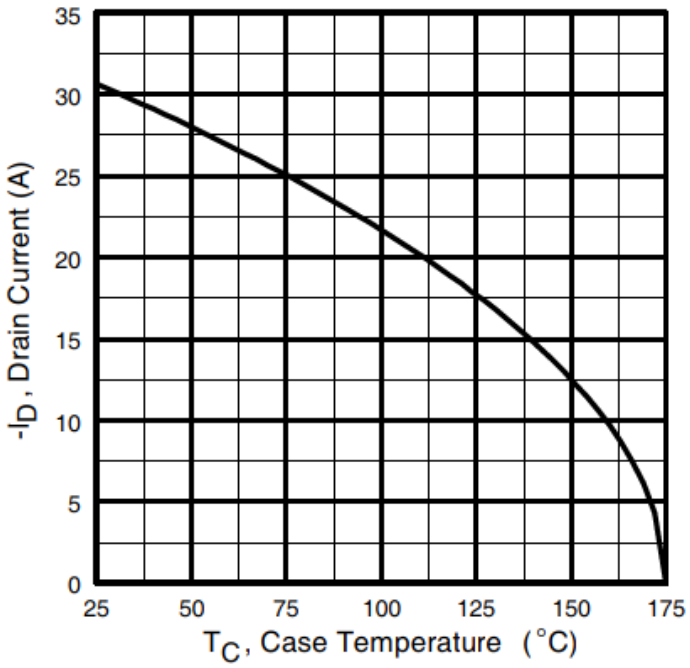


Fig 9. Maximum Drain Current vs. Case Temperature

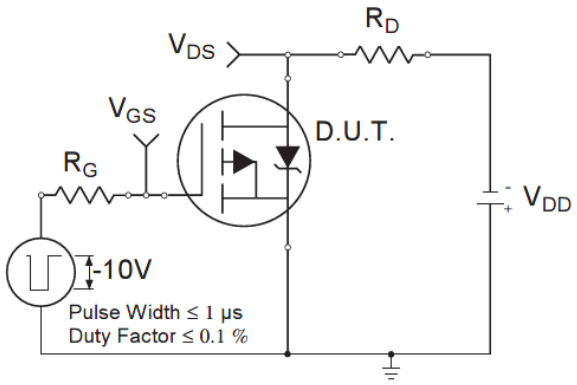


Fig 10a. Switching Time Test Circuit

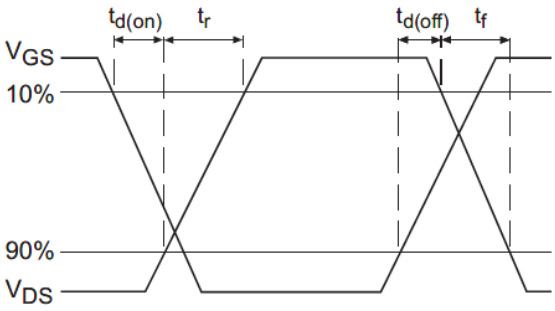


Fig 10a. Switching Time Waveforms

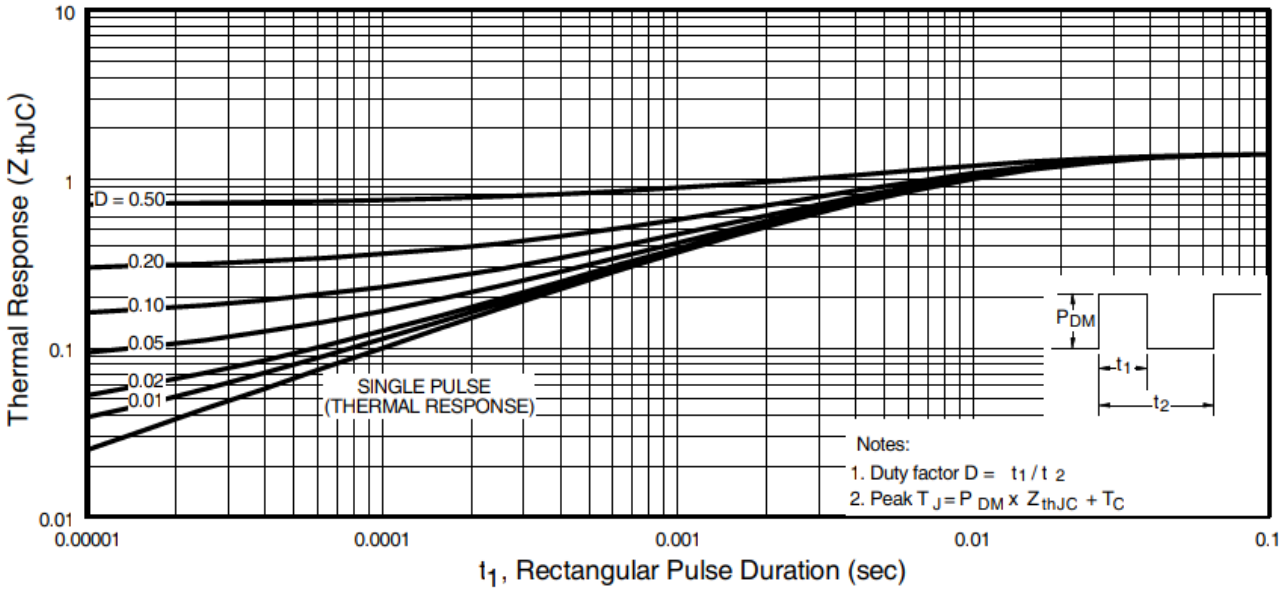


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

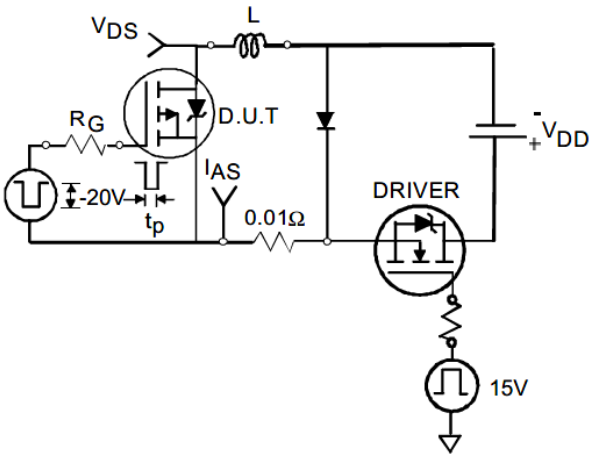


Fig. 12a. Unclamped Inductive Test Circuit

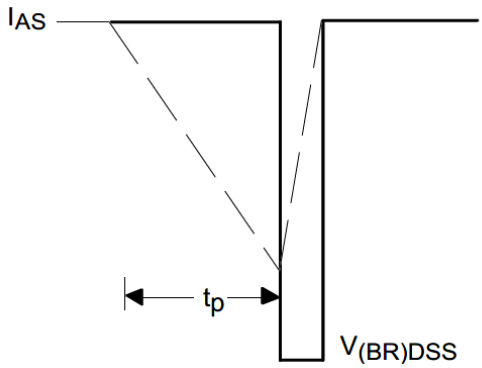


Fig. 12b. Unclamped Inductive Waveforms

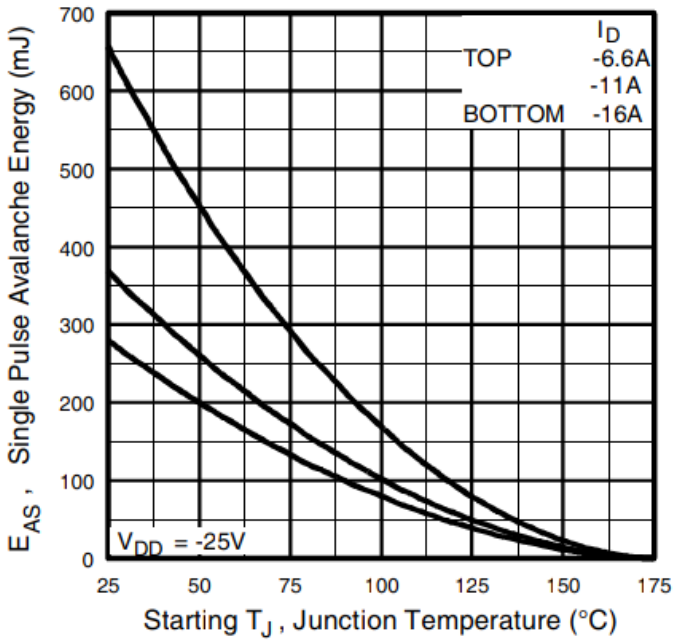


Fig 12c. Maximum Avalanche Energy vs. Drain Current

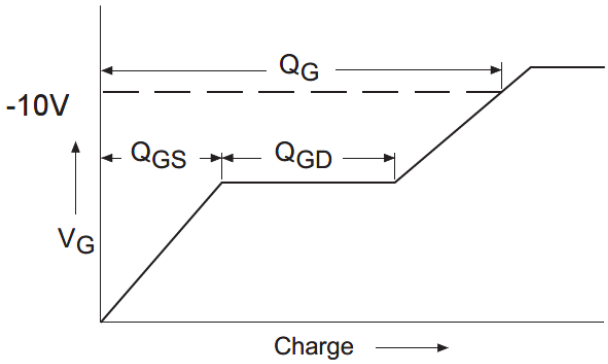


Fig 13a. Basic Gate Charge Waveform

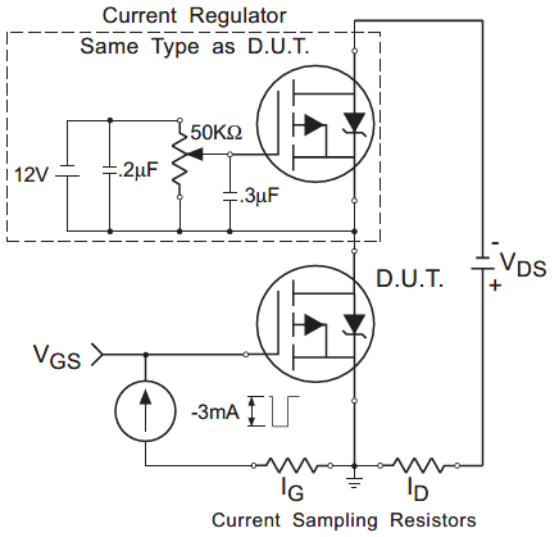


Fig 13b. Gate Charge Test Circuit

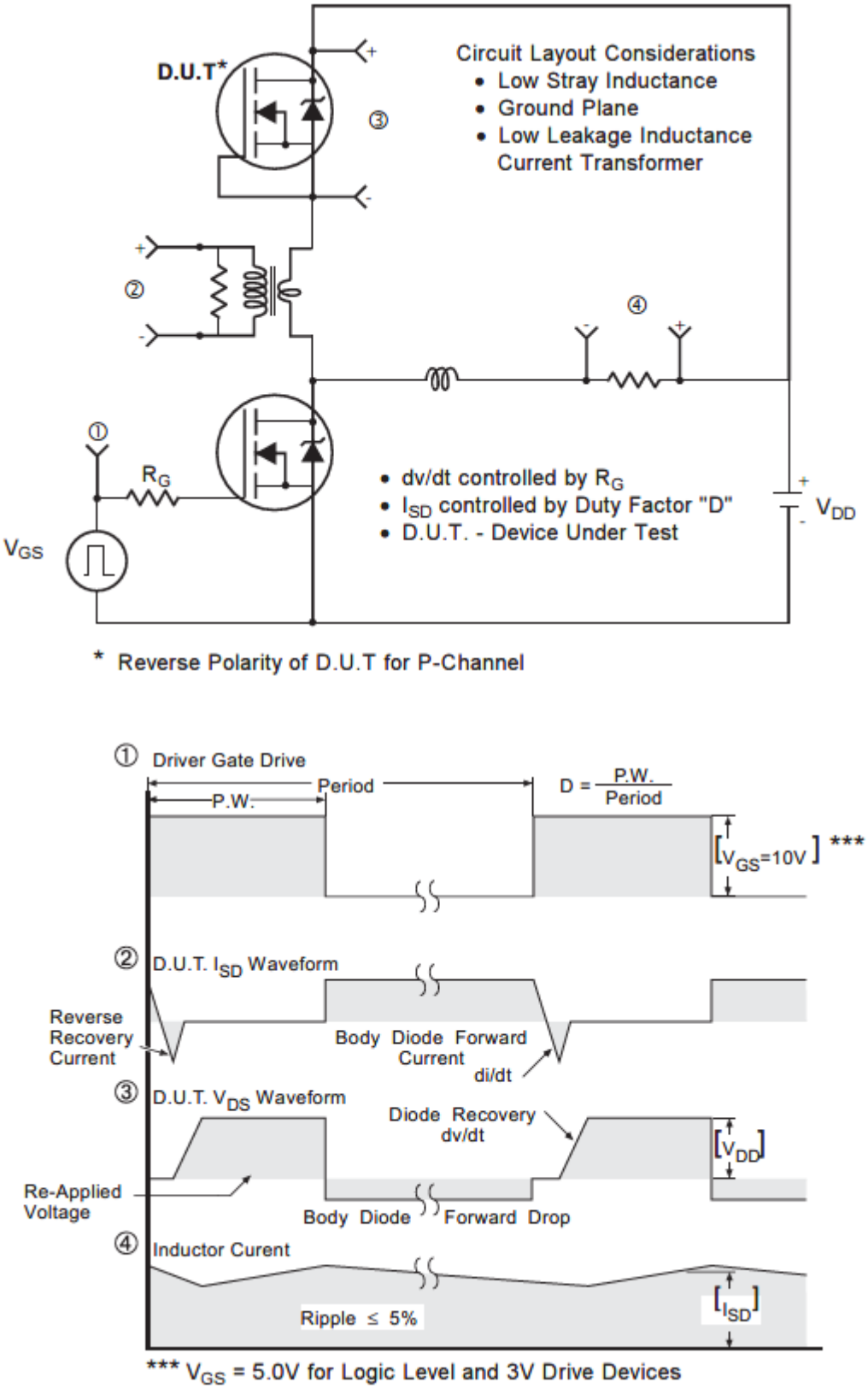
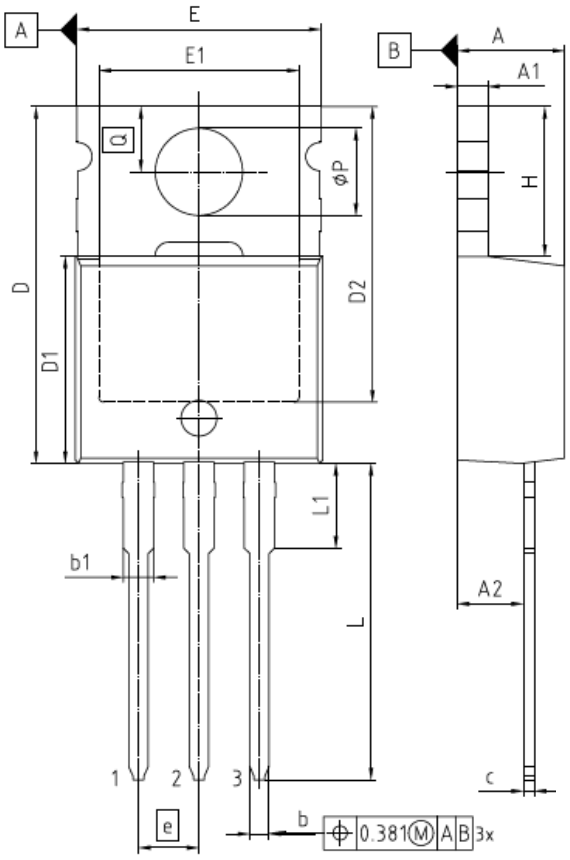


Fig 14. Peak Diode Recovery dv/dt Test Circuit for P-Channel
HEXFET® Power MOSFETs

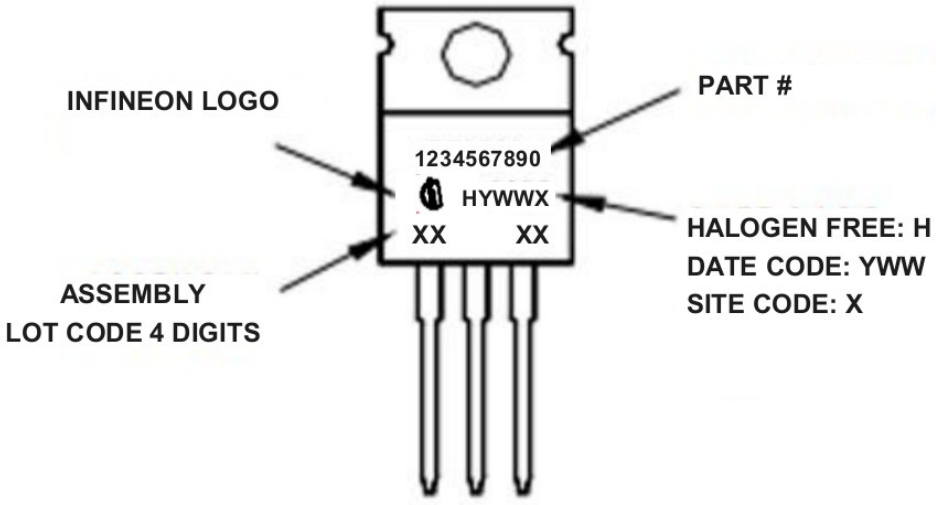
TO-220 Package Outline (Dimensions are shown in millimeters (inches))



NOTES:
DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS
GATE BURRS ARE LESS THAN 0.5 mm

PACKAGE - GROUP NUMBER:	PG-TO220-3-U05	
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	3.56	4.83
A1	1.14	1.40
A2	2.03	2.92
b	0.38	1.01
b1	1.14	1.78
c	0.36	0.61
D	14.22	16.51
D1	8.38	9.20
D2	11.68	12.88
E	9.65	10.67
E1	6.86	8.89
e	2.54	
N	3	
H	5.84	6.86
L	12.70	14.73
L1	3.56	4.06
øP	3.54	4.08
Q	2.54	3.42

TO-220 Part Marking Information



TO-220 packages are not recommended for Surface Mount Application.

Revision History

Date	Rev.	Comments
2026-07-24	2.1	• Update datasheet to Infineon format • Updated Package Outline and Part marking –page 8 • Added disclaimer on last page.

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